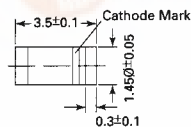


### Silicon Epitaxial Planar Diode Switches

In MiniMELF case especially suited for automatic insertion for electronic band-switching in radio and TV tuners in the frequency range of 50 ... 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.

These diodes are delivered taped.  
Details see "Taping".



Glass case MiniMELF

Weight approx. 0.05g  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current at $T_{amb} = 25\text{ }^\circ\text{C}$	$I_F$	100	mA
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-55 to + 150	$^\circ\text{C}$



# BA682, BA683

Characteristics at  $T_{amb} = 25\text{ }^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	-	-	1	V
Leakage Current at $V_R = 20\text{ V}$	$I_R$	-	-	50	nA
Dynamic Forward Resistance at $f = 50\text{ to }1000\text{ MHz}$ , $I_F = 3\text{ mA}$ at $f = 50\text{ to }1000\text{ MHz}$ , $I_F = 10\text{ mA}$	<b>BA682</b> $r_f$	-	-	0.7	$\Omega$
	<b>BA683</b> $r_f$	-	-	1.2	$\Omega$
	<b>BA682</b> $r_f$	-	-	0.5	$\Omega$
	<b>BA683</b> $r_f$	-	-	0.9	$\Omega$
Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$ at $V_R = 3\text{ V}$ , $f = 1\text{ MHz}$	<b>BA682</b> $C_{tot}$	-	-	1.5	pF
	<b>BA683</b> $C_{tot}$	-	-	1.25	pF
	<b>BA683</b> $C_{tot}$	-	-	1.2	pF
Series Inductance	$L_s$	-	2	-	nH

